

MMAD1105 and MMAD1105e3

Switching Diode Array Steering Diode TVS Array™

		DES	CRIP	ΓΙΟΝ					APPEARA	NCE
fabricated by steering dio surge by dir external TV ground to pu fast switchin equipment s etc., as well advantages improved re smaller footp that may no with either T matte-Tin fin *See MMA	y a planar p des protectin ecting them S diode ma revent overv g core-drive uch as mage as decodin of integrat eliability. Th print, smaller brint, smaller to as use in-Lead plat hish by addin AD1106(e3) f	process an ing up to e to the pose ay be add voltage on r application netic cores g or encoor ted circuit his is a re- r weight, a r friendly i ing termina- ag an "e3" s for directing	d mour eight I/C sitive si led bet the su ons. This s, thin-fi ding ap s such esult of nd elim n PC b ations c suffix to g negat	nted in O ports de of the tween t pply rai is incluce ilm memo pplication h as h f fewer hination f fewer hination f as Rc o the par tive tran	a 14-pi from p he pose he pose l. They les com nories, ns. The nigh-den pick a of varic ounting bHS Co rt numb sients t	n packa positive er suppl itive su may al puters plated-w ese arra nsity pa ous disc pus disc pus disc pus disc pus disc pus disc ous disc		s r 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 2 3 4 5 6 7 Viewing P	14 13 12 11 10 9 8 in Layout
PORTANT: For		nt data, const TURES	ult MICR	OSEMI's	website:	http://w	ww.microsemi.co	om ATIONS /	DENEELT	
 UL 94V-0 Low Capa Switching RoHS Cor IEC 61000 61000 61000 	rray I-Pin SOIC Pa Flammability citance 1.5 pf speeds less t mpliant device)-4 compatible)-4-2 (ESD): A)-4-4 (EFT): 4)-4-5 (surge):	Classification F per diode han 5 ns es available e Air 15kV, cou 0A – 5/50 n	by addii ntact – 8 s	-	suffix	fre • RS • Et • Co • LA	w capacitance equency data lin S-232 & RS-422 hernet: 10 Base omputer I / O P N witching Core D	es 2 Interface Ne e T orts	-	or high
	MAXIMU						MECHAN	ICAL AND	PACKAGI	NG
 Storage Te Forward S Continuou Power Dis Solder Ter 	Temperature: emperature: -{ urge Current: s Forward Cu sipation (P _D): mperatures: 2	55°C to +15 2 Amps (8 12 Amps (8 rrent: 400 m 1500 mW (1 260°C for 10	0°C 3.3 ms) 8/20 µs) nA (one total) 0 s (max	diode) timum)		ei cl • T au 7% • M au in • W • T	ASE: Void-free poxy body meet assification ERMINALS: Tiinnealed matte-7 50 method 2026 IARKING: MSC nd date code. F dent on top of p /EIGHT: 0.127 (ape & Reel pac Carrier tube pacl	ting UL94V-0 n-Lead or Rol Fin plating sol book Pin #1 is to the backage grams (appro: kaging: 2500 kaging: 55 pc:	flammability HS Compliant derable per M 1105 or MMA e left of the do ximate) pcs (STANDA s	IIL-STD- D1105e3 ot or
ELECTRI	CAL CHAR	RACTERI	STICS	PER L	.INE @	25°C	Unless othe	erwise spe	ecified	
PART NUMBER	BREAKDOWN VOLTAGE V _{BR} @ I _{BR} =100µA V	WORKING PEAK REVERSE VOLTAGE V _{RWM} V	LEAKAGE CURRENT I _R T _A = 25°C μΑ		LEAKAGE CURRENT I _R T _A = 150°C µA		CAPACITANCE C @ 0 V pF	REVERSE RECOVERY TIME t _{rr} ns	FORWARD VOLTAGE V_F $I_F = 10 \text{ mA}$ V	FORWARD VOLTAGE V_F $I_F = 100 \text{ mA}$ V
	MIN	MAX	MAX	@V _R	MAX	@V _R	TYP	MAX	MAX	MAX
MMAD1105 MMAD1105e3	90	75	0.200	20	300	20	1.5	5.0	1.00	1.20

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Switching Diode Array Steering Diode TVS Array™

	SYMBOLS & DEFINITIONS				
Symbol	Definition				
V _{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.				
V _{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.				
VF	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.				
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.				
С	Capacitance: The capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.				

OUTLINE AND CIRCUIT



	INC	CHES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
А	0.336	0.344	8.53	8.74	
В	0.150	0.158	3.81	4.01	
С	0.053	0.069	1.35	1.75	
D	0.011	0.021	0.28	0.53	
F	0.016	0.050	0.41	1.27	
G	0.050) BSC	01.27 BSC		
J	0.006	0.010	0.15	0.25	
K	0.004	0.008	0.10	0.20	
L	0.189	0.206	4.80	5.23	
Р	0.228	0.244	5.79	6.19	







CIRCUIT CONFIGURATION